



5N60

600V N-Channel Power MOSFET

Features

- $R_{DS(ON)} < 2.2\Omega$ @ $V_{GS}=10V, I_D=2.5A$
- Fast switching capability
- Lead free in compliance with EU RoHS
- directive. Green molding compound

Mechanical Data

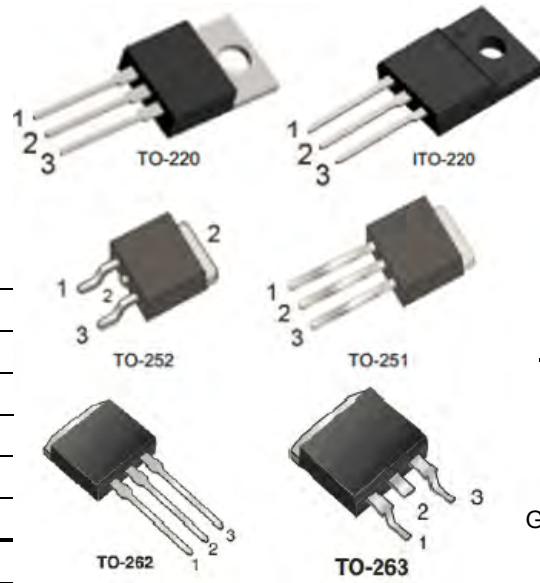
- Case: TO-251, TO-252, TO-220, ITO-220
TO-262, TO-263 Package

Ordering Information

Part No.	Package	Packing
DMP5N60-TU	TO-251	75pcs / Tube
DMD5N60-TR	TO-252	2.5Kpcs / 13" Reel
DMD5N60-TU	TO-252	75pcs / Tube
DMT5N60-TU	TO-220	50pcs / Tube
DMF5N60-TU	ITO-220	50pcs / Tube
DMK5N60-TU	TO-262	50pcs / Tube
DMG5N60-TU	TO-263	50pcs / Tube
DMG5N60-TR	TO-263	800pcs / 13" Reel

PRODUCT SUMMARY

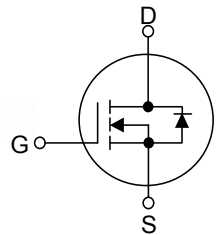
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)
600	2.2 @ $V_{GS}=10V$	5



Pin Definition:

1. Gate
2. Drain
3. Source

Block Diagram



ABSOLUTE MAXIMUM RATINGS ($T_C=25^\circ C$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	600	V
Gate-Source Voltage		V_{GSS}	± 30	V
Continuous Drain Current		I_D	5.0	A
Pulsed Drain Current (Note 2)		I_{DM}	20	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	210	mJ
Power Dissipation	TO-220/TO-262/TO-263	P_D	100	W
	ITO-220		36	W
	TO-251/TO-252		54	W
Junction Temperature		T_J	+150	$^\circ C$
Operating Temperature		T_{OPR}	-55 ~ +150	$^\circ C$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ C$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature

3. $L = 16.8mH$, $I_{AS} = 5A$, $V_{DD} = 50V$, $R_G = 25\Omega$, Starting $T_J = 25^\circ C$



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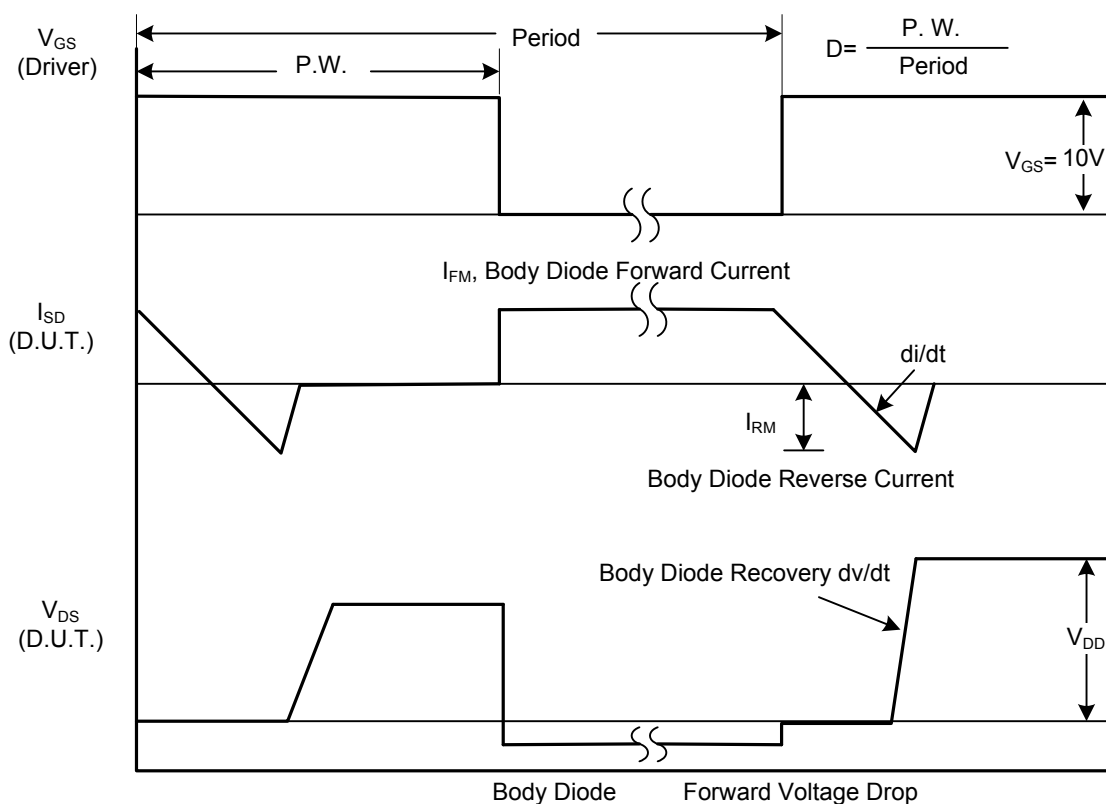
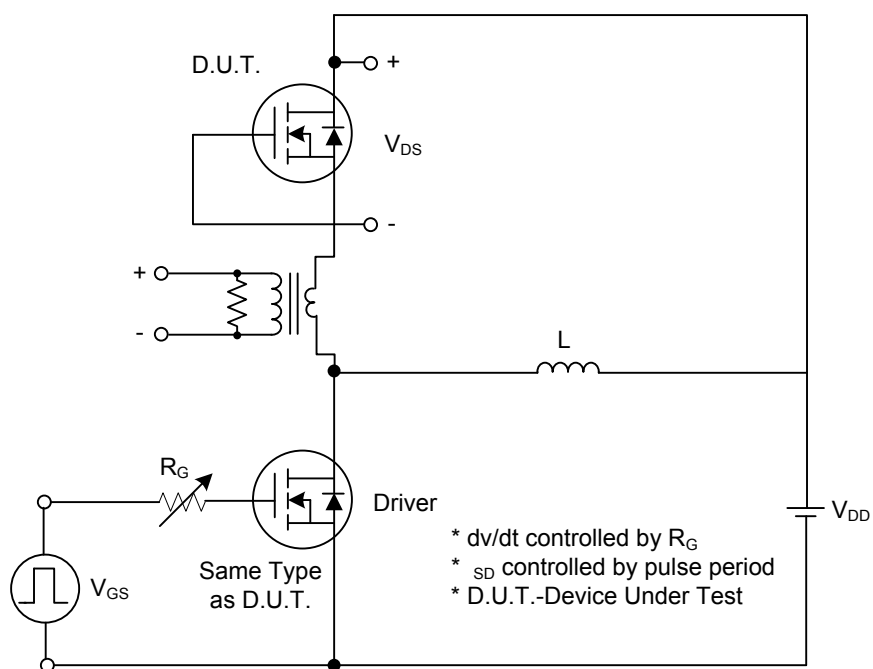
THERMAL DATA

PARAMETER		SYMBOL	RATING	UNIT
Junction to Ambient	TO-220/ITO-220 TO-262/TO-263	θ_{JA}	62.5	°C/W
	TO-251/ TO-252		110	
Junction to Case	TO-220/ITO-220 TO-262/TO-263	θ_{JC}	2.35	°C/W
	ITO-220		5.5	
	TO-251/ TO-252		2.9	

ELECTRICAL CHARACTERISTICS ($T_C=25^\circ\text{C}$, unless otherwise specified)

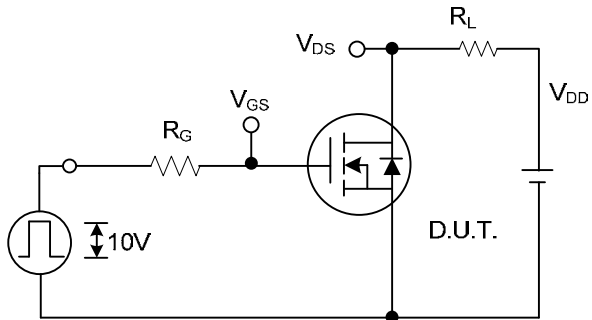
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	V _{GS} = 0V, I _D = 250μA	600			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} = 600V, V _{GS} = 0V			1	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} = 30V, V _{DS} = 0V			100	nA
	Reverse		V _{GS} = -30V, V _{DS} = 0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V,I _D = 2.5A		1.9	2.2	Ω
DYNAMIC CHARACTERISTICS							
Input Capacitance		C _{ISS}	V _{DS} = 25V, V _{GS} = 0V, f = 1MHz		520		pF
Output Capacitance		C _{OSS}			70		pF
Reverse Transfer Capacitance		C _{RSS}			7		pF
SWITCHING CHARACTERISTICS							
Turn-On Delay Time		t _{D(ON)}	V _{DD} = 300V, I _D =5A, R _G = 25Ω (Note 1, 2)		20		ns
Turn-On Rise Time		t _R			70		ns
Turn-Off Delay Time		t _{D(OFF)}			60		ns
Turn-Off Fall Time		t _F			120		ns
Total Gate Charge		Q _G	V _{DS} = 480V,I _D = 5.0A, V _{GS} = 10V (Note 1, 2)		20		nC
Gate-Source Charge		Q _{GS}			1.5		nC
Gate-Drain Charge		Q _{GD}			10		nC
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Drain-Source Diode Forward Voltage		V _{SD}	V _{GS} =0V,I _S =5A			1.4	V
Maximum Continuous Drain-Source Diode Forward Current		I _S				5	A
Maximum Pulsed Drain-Source Diode Forward Current		I _{SM}				20	A
Reverse Recovery Time		t _{rr}	V _{GS} = 0 V, I _S = 5A,		300		ns
Reverse Recovery Charge		Q _{RR}	dl _F /dt = 100 A/ μs (Note 1)		2.2		μC

Notes: 1. Pulse Test: Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$
2. Essentially independent of operating temperature

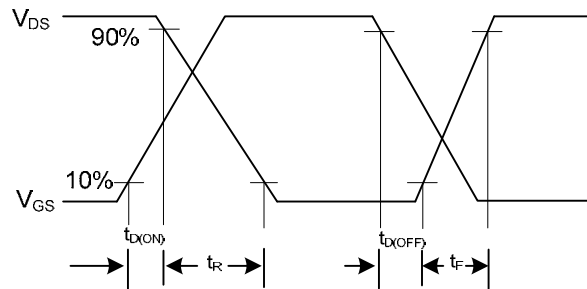




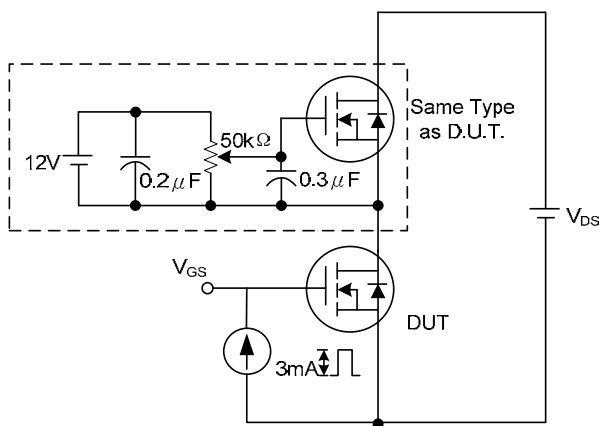
TEST CIRCUITS AND WAVEFORMS(Cont.)



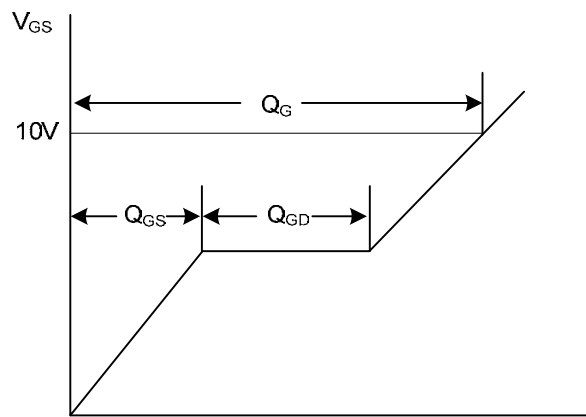
Switching Test Circuit



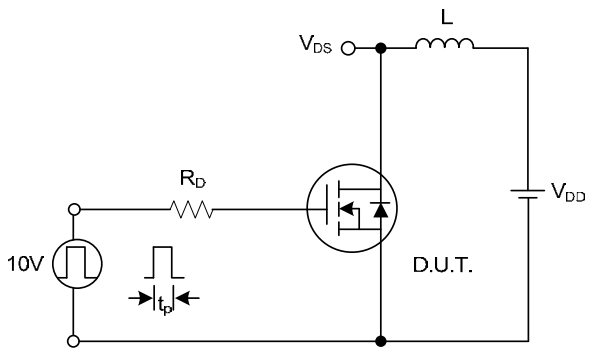
Switching Waveforms



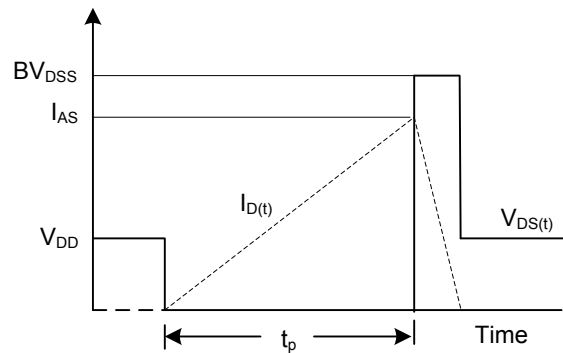
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



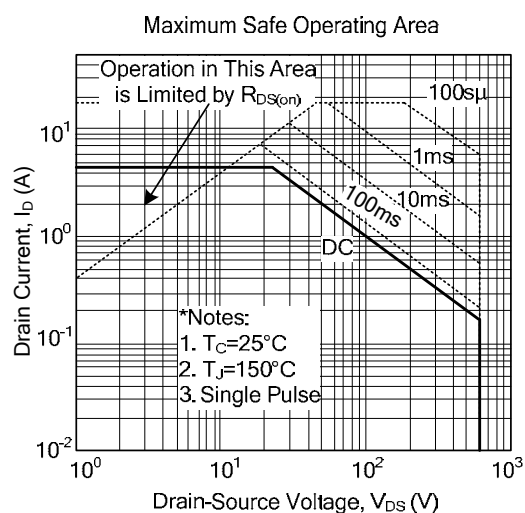
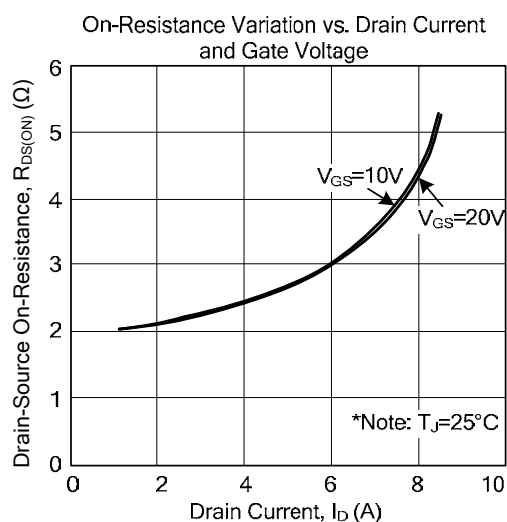
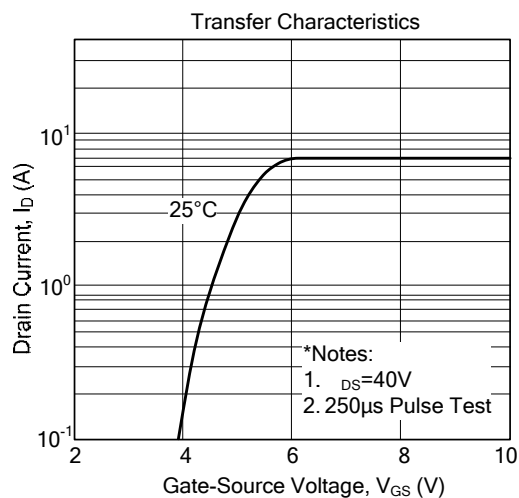
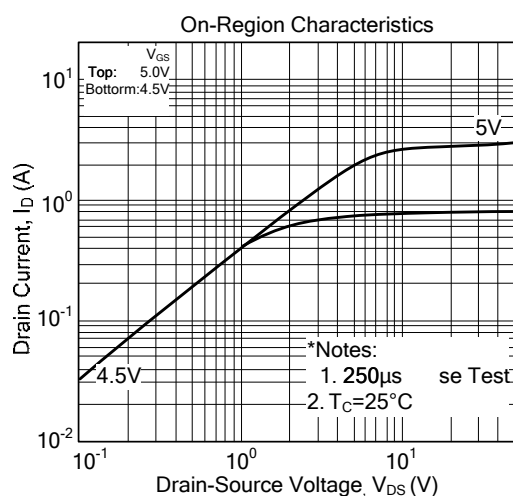
Unclamped Inductive Switching Waveforms



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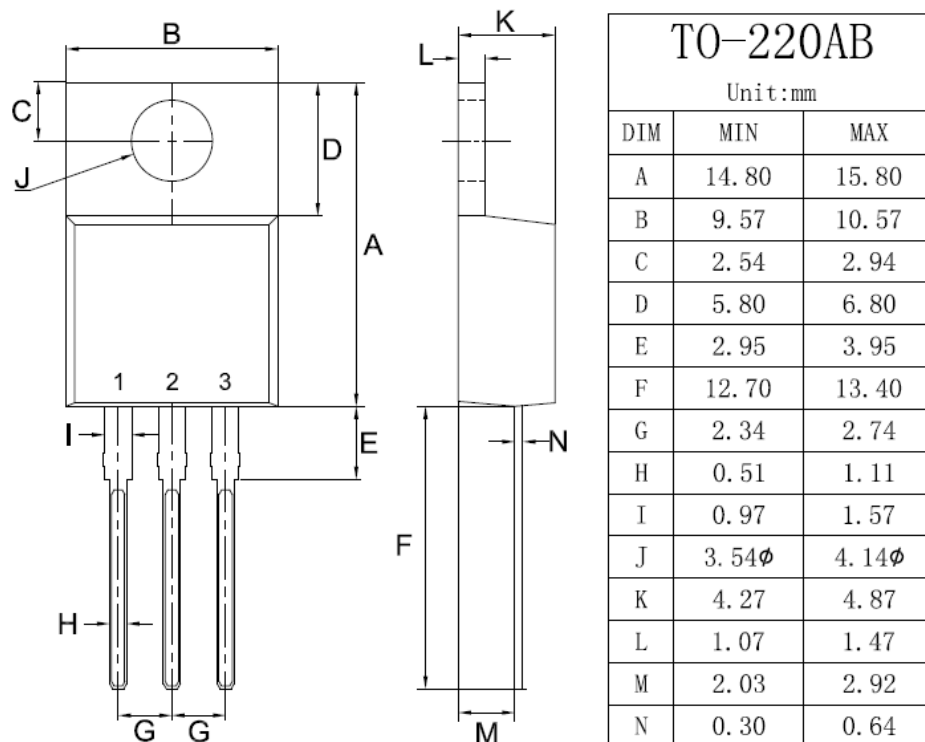
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TYPICAL CHARACTERISTICS

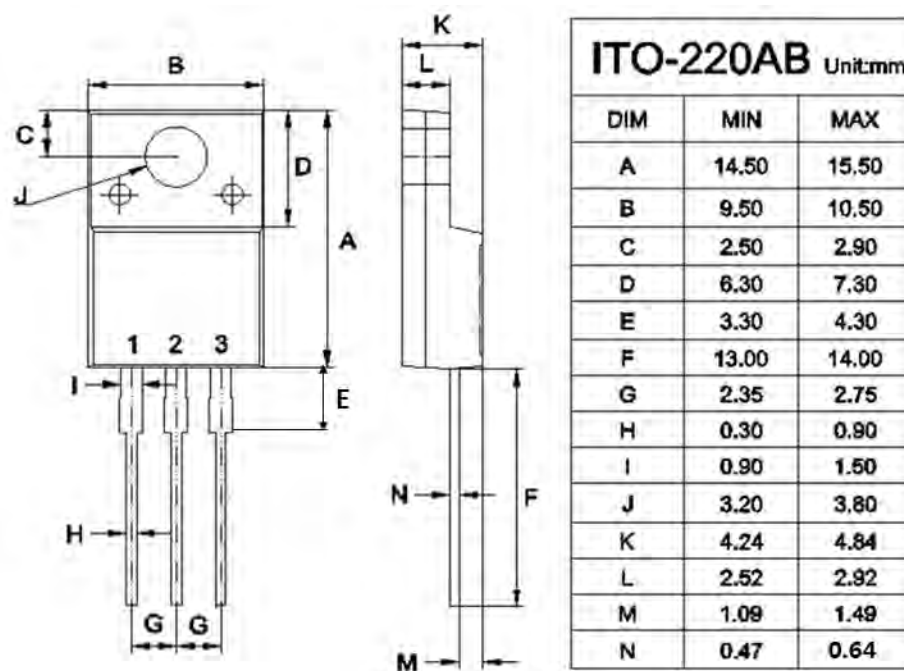




TO-220 Mechanical Drawing



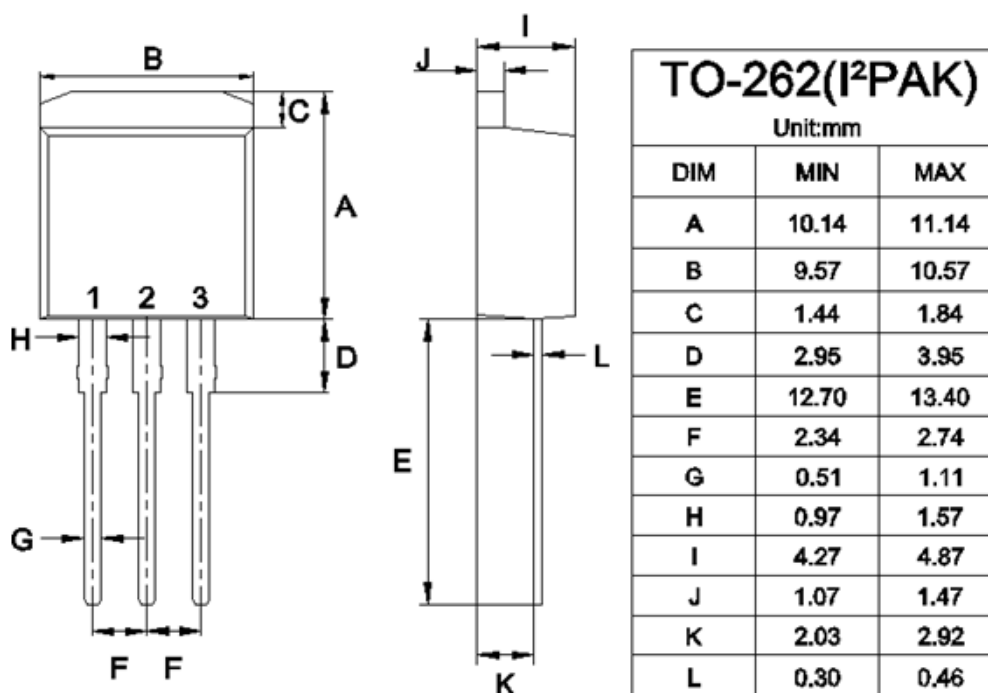
ITO-220 Mechanical Drawing



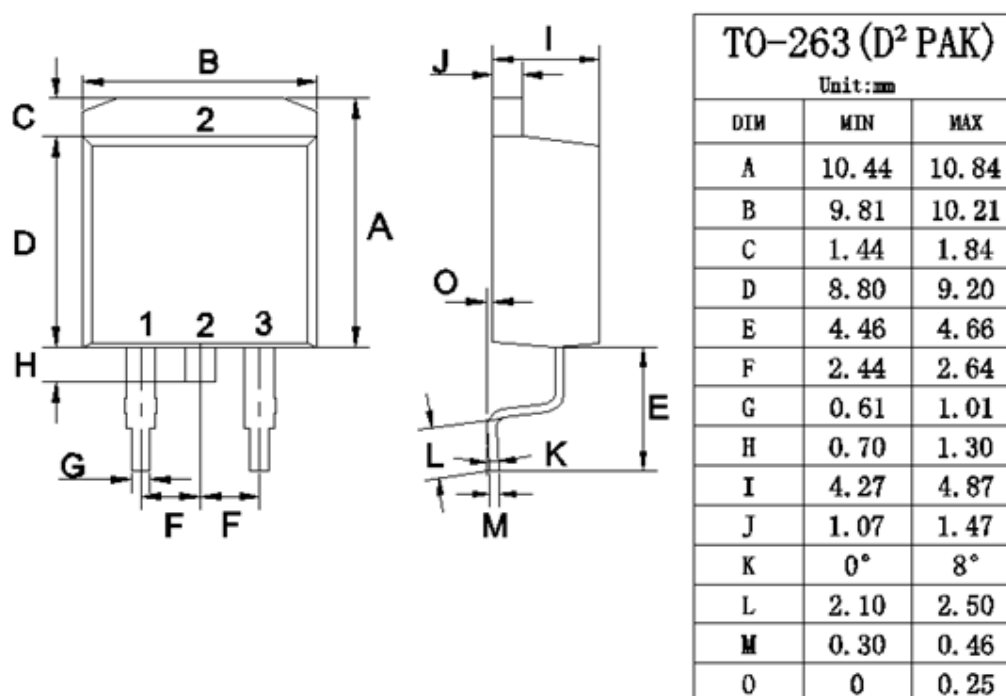
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TO-262 Mechanical Drawing



TO-263 Mechanical Drawing

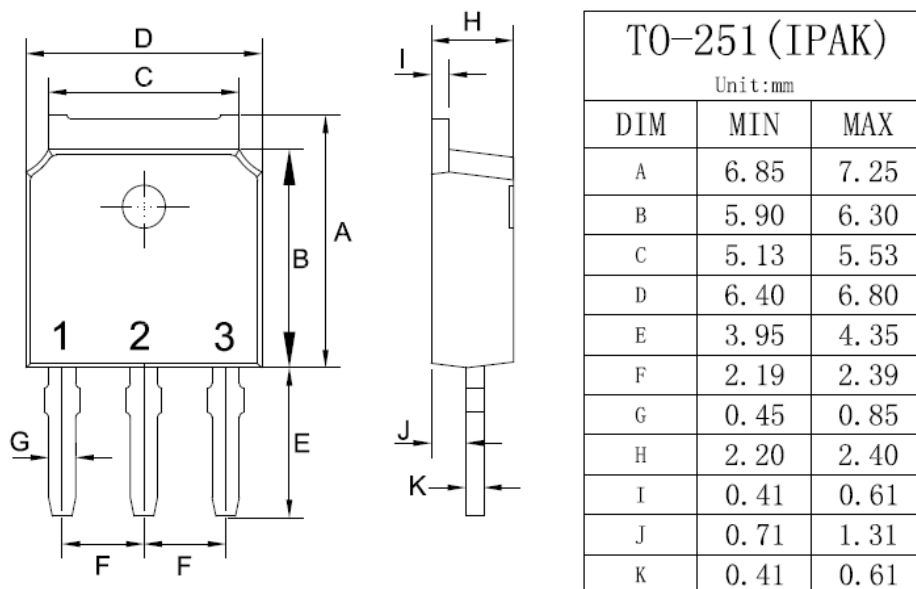




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TO-251 Mechanical Drawing



TO-252 Mechanical Drawing

